



گروه فنی مهندسی جوش و برش مقدم

اعتماد از شما کیفیت و تخصص از ما



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برای کسب اطلاعات بیشتر بر روی لینک ها کلیک کنید

- 7 سال سابقه آموزش تعمیرات تخصصی دستگاه های جوش اینورتری تک فاز و 3 فاز
- 7 سال سابقه فروش قطعات الکترونیکی دستگاه جوش تک فاز و 3 فاز
- آموزش تخصصی تحلیل دستگاه های جوش اینورتری مختص ابراز فروشان
- آموزش تخصصی ابراز آلات شارژی

isc N-Channel MOSFET Transistor

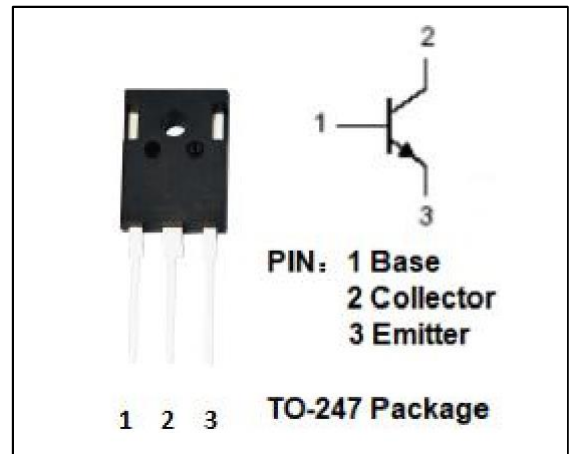
23N50

FEATURES

- Drain Current $-I_D = 23A @ T_C = 25^\circ C$
- Drain Source Voltage-
: $V_{DSS} = 500V (Min)$
- Static Drain-Source On-Resistance
: $R_{DS(on)} = 0.245 \Omega (Max)$
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRIPTION

- Designed for use in switch mode power supplies and general purpose applications.

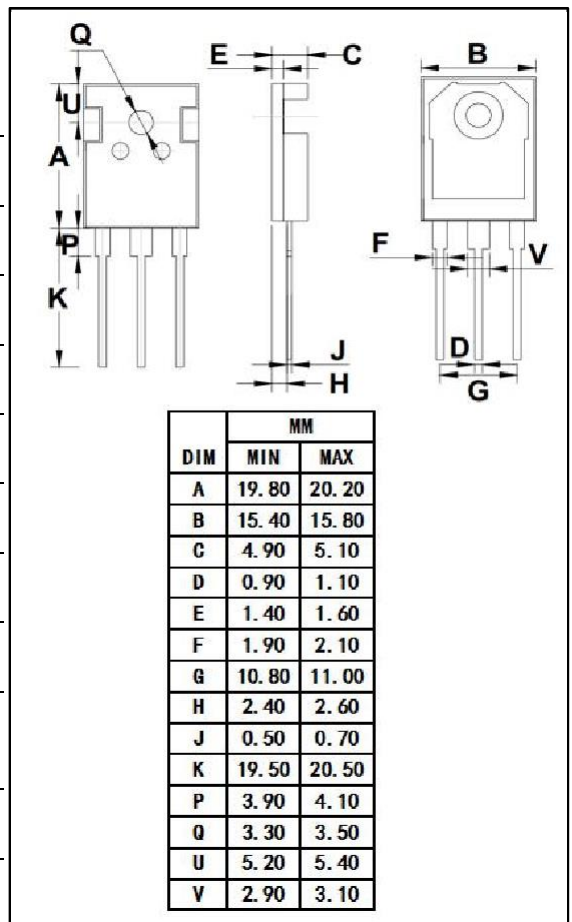


ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ C$)

| SYMBOL | PARAMETER | VALUE | UNIT |
|-----------|--|----------|------------|
| V_{DSS} | Drain-Source Voltage | 500 | V |
| V_{GS} | Gate-Source Voltage-Continuous | ± 30 | V |
| I_D | Drain Current-Continuous | 23 | A |
| I_{DM} | Drain Current-Single Pulse | 92 | A |
| P_D | Total Dissipation @ $T_C = 25^\circ C$ | 315 | W |
| T_J | Max. Operating Junction Temperature | -55~150 | $^\circ C$ |
| T_{stg} | Storage Temperature | -55~150 | $^\circ C$ |

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | MAX | UNIT |
|--------------|--------------------------------------|------|--------------|
| $R_{th j-c}$ | Thermal Resistance, Junction to Case | 0.40 | $^\circ C/W$ |



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ELECTRICAL CHARACTERISTICS

 $T_C=25^\circ\text{C}$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | MAX | UNIT |
|---------------|---------------------------------|--|-----|-----------|---------------|
| $V_{(BR)DSS}$ | Drain-Source Breakdown Voltage | $V_{GS}=0; I_D=0.25\text{mA}$ | 500 | | V |
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{DS}=V_{GS}; I_D=2.5\text{mA}$ | 2.5 | 3.5 | V |
| $R_{DS(on)}$ | Drain-Source On-Resistance | $V_{GS}=10\text{V}; I_D=11.5\text{A}$ | | 0.245 | Ω |
| I_{GSS} | Gate-Body Leakage Current | $V_{GS}=\pm 30\text{V}; V_{DS}=0$ | | ± 100 | nA |
| I_{DSS} | Zero Gate Voltage Drain Current | $V_{DS}=500\text{V}; V_{GS}=0$ $V_{DS}=400\text{V}; V_{GS}=0@T_C=125^\circ\text{C}$ | | 25 250 | μA |
| V_{SD} | Forward On-Voltage | $I_S=-23\text{A}; V_{GS}=0$ | | 1.35 | V |

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